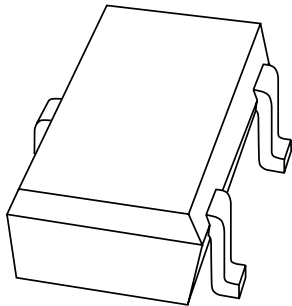


DATA SHEET



PMST2222; PMST2222A NPN switching transistors

Product specification
Supersedes data of 1997 Jul 14

1999 Apr 22

NPN switching transistors

PMST2222; PMST2222A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- High-speed switching and linear amplification.

DESCRIPTION

NPN switching transistor in a SOT323 plastic package.
PNP complement: PMST2907A.

MARKING

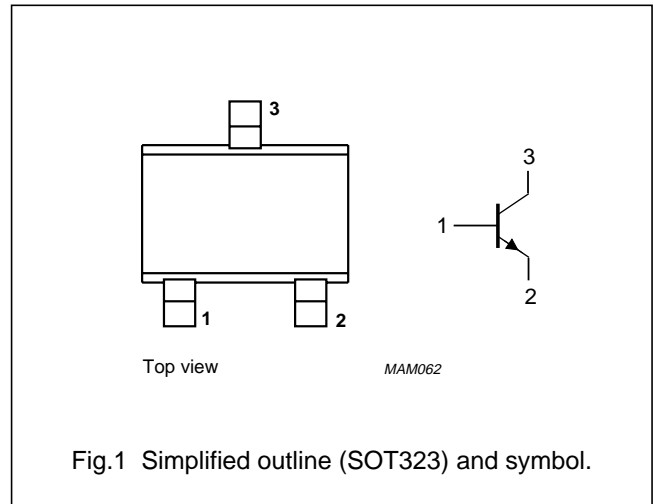
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMST2222	*1B
PMST2222A	*1P

Note

- * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter			
	PMST2222		–	60	V
	PMST2222A		–	75	V
V _{CEO}	collector-emitter voltage	open base			
	PMST2222		–	30	V
	PMST2222A		–	40	V
V _{EBO}	emitter-base voltage	open collector			
	PMST2222		–	5	V
	PMST2222A		–	6	V
I _C	collector current (DC)		–	600	mA
I _{CM}	peak collector current		–	800	mA
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN switching transistors

PMST2222; PMST2222A

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current PMST2222	$I_E = 0; V_{CB} = 50\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 50\text{ V}; T_j = 125\text{ °C}$	–	10	μA
	collector cut-off current PMST2222A	$I_E = 0; V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_j = 125\text{ °C}$	–	10	μA
I_{EBO}	collector cut-off current	$I_C = 0; V_{EB} = 3\text{ V}$	–	10	nA
h_{FE}	DC current gain	$I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$	35	–	
		$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$	50	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	75	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = -55\text{ °C}$	35	–	
		$I_C = 150\text{ mA}; V_{CE} = 1\text{ V}; \text{note 1}$	50	–	
	$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	100	300		
	DC current gain PMST2222 PMST2222A	$I_C = 500\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$	30 40	– –	
V_{CEsat}	collector-emitter saturation voltage PMST2222	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	400	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	1.6	V
	collector-emitter saturation voltage PMST2222A	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	300	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	1	V
V_{BEsat}	base-emitter saturation voltage PMST2222	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	1.3	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	2.6	V
	base-emitter saturation voltage PMST2222A	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	0.6	1.2	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	2	V
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	8	pF
C_e	emitter capacitance PMST2222 PMST2222A	$I_C = i_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	30	pF
			–	25	pF
f_T	transition frequency PMST2222 PMST2222A	$I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	250	–	MHz
			300	–	MHz

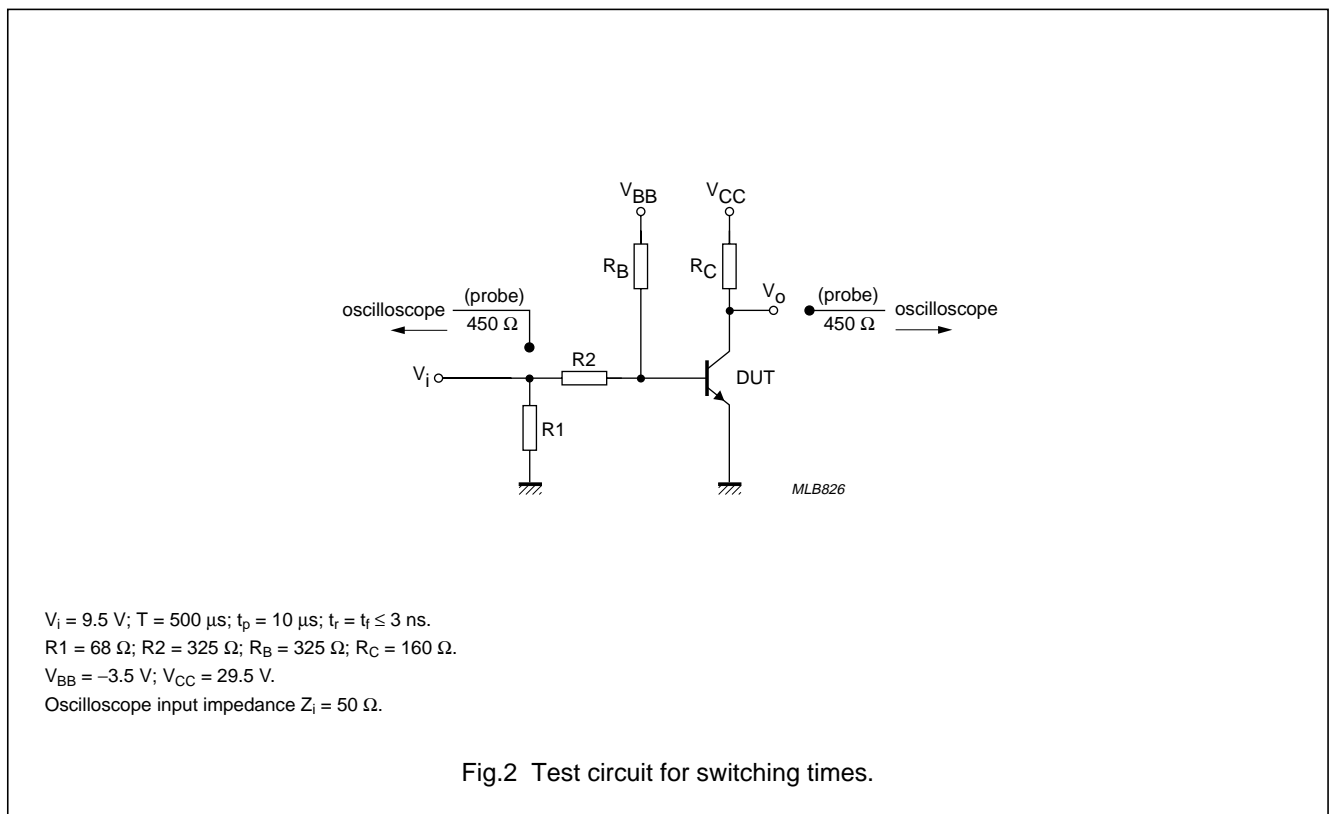
NPN switching transistors

PMST2222; PMST2222A

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
F	noise figure	$I_C = 200 \mu A$; $V_{CE} = 5 V$; $R_S = 2 k\Omega$; $f = 1 kHz$; $B = 200 Hz$	–	4	dB
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	$I_{Con} = 150 mA$; $I_{Bon} = 15 mA$; $I_{Boff} = -15 mA$	–	35	ns
t_d	delay time		–	15	ns
t_r	rise time		–	20	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

Note

1. Pulse test: $t_p \leq 300 \mu s$; $\delta \leq 0.02$.



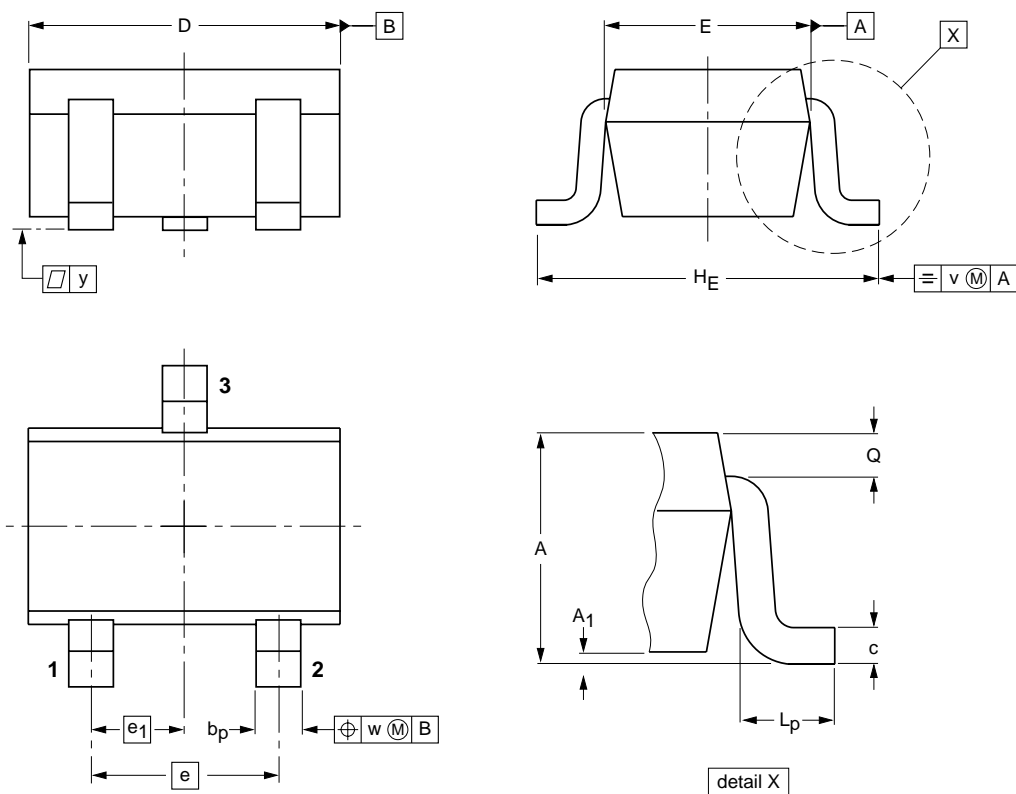
NPN switching transistors

PMST2222; PMST2222A

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN switching transistors

PMST2222; PMST2222A

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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NPN switching transistors

PMST2222; PMST2222A

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